

### General Description

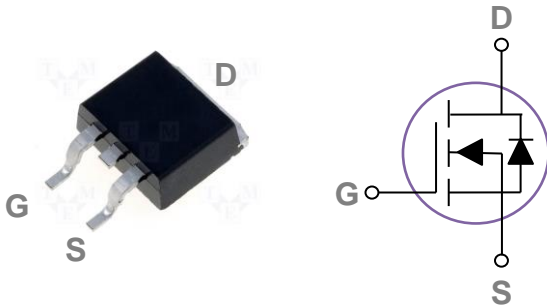
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
100V	2.2mΩ	260A

### Features

- 100V,260A,  $R_{DS(ON)} = 2.2m\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### TO263 Pin Configuration



### Applications

- Networking
- Load Switch
- LED applications
- Quick Charger

### Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	+20/-12	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ C$ )	260	A
	Drain Current – Continuous ( $T_c=100^\circ C$ )	164	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	1040	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	1050	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	145	A
$P_D$	Power Dissipation ( $T_c=25^\circ C$ )	416	W
	Power Dissipation – Derate above $25^\circ C$	3.3	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-50 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-50 to 150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.3	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V	---	---	100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	---	1.8	2.2	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	---	2.4	3	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	---	24	---	S

**Dynamic and switching Characteristics**

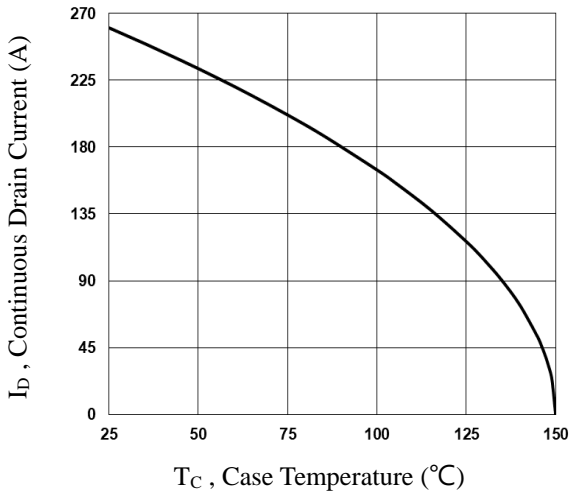
Q <sub>g</sub>	Total Gate Charge <sup>3,4</sup>	V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	192	380	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3,4</sup>		---	27	54	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3,4</sup>		---	24	48	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3,4</sup>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =1A	---	46	92	ns
T <sub>r</sub>	Rise Time <sup>3,4</sup>		---	64	128	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3,4</sup>		---	320	640	
T <sub>f</sub>	Fall Time <sup>3,4</sup>		---	230	460	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	13300	26000	pF
C <sub>oss</sub>	Output Capacitance		---	3380	6700	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	156	300	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	1.1	---	Ω

**Drain-Source Diode Characteristics and Maximum Ratings**

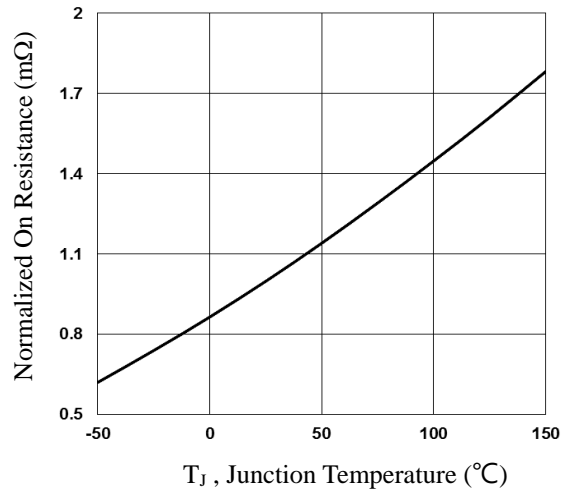
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	260	A
I <sub>SM</sub>	Pulsed Source Current		---	---	520	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time <sup>3</sup>	I <sub>S</sub> =20A, di/dt=100A/μs T <sub>J</sub> =25°C	---	98	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge <sup>3</sup>		---	304	---	nC

Note :

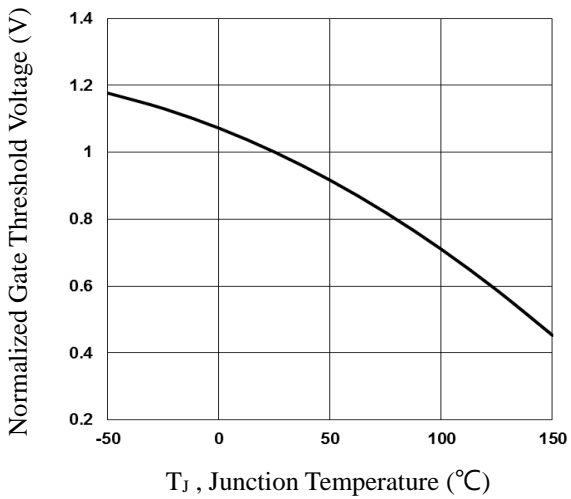
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=145A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



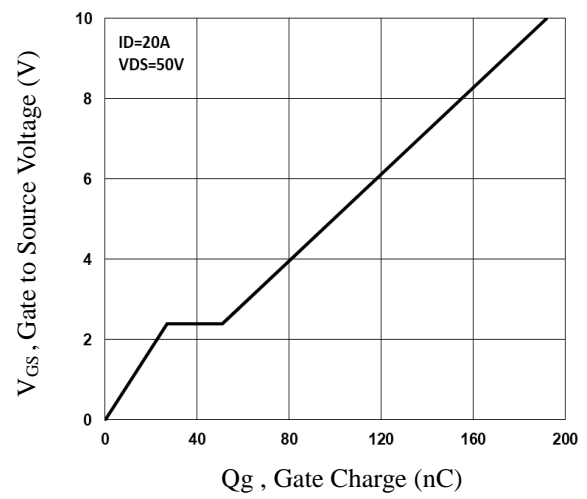
**Fig.1 Continuous Drain Current vs.  $T_C$**



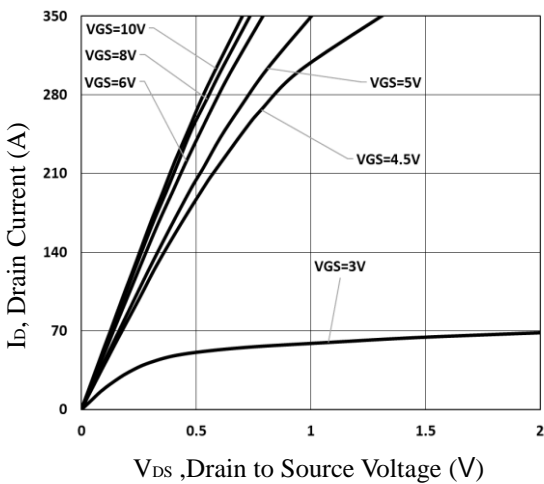
**Fig.2 Normalized  $R_{DSON}$  vs.  $T_J$**



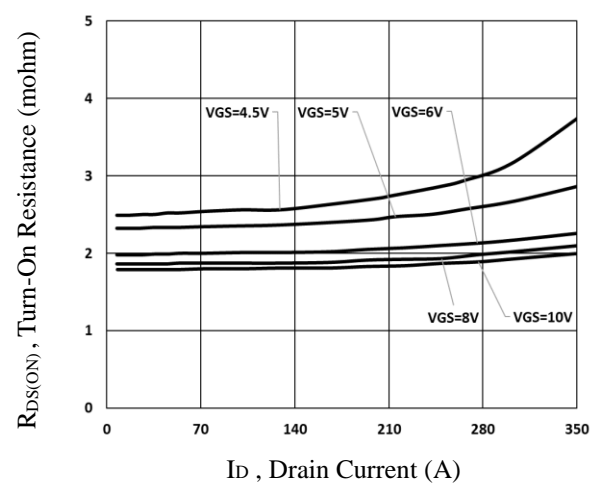
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



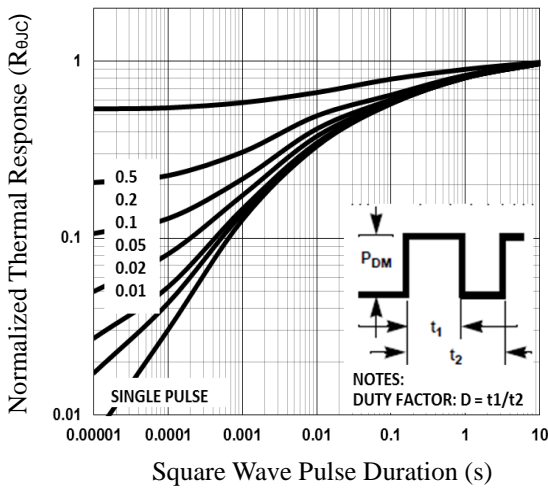
**Fig.4 Gate Charge Characteristics**



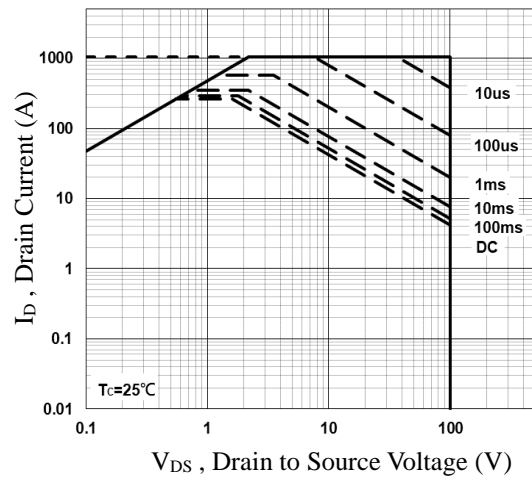
**Fig.5 Typical Output Characteristics**



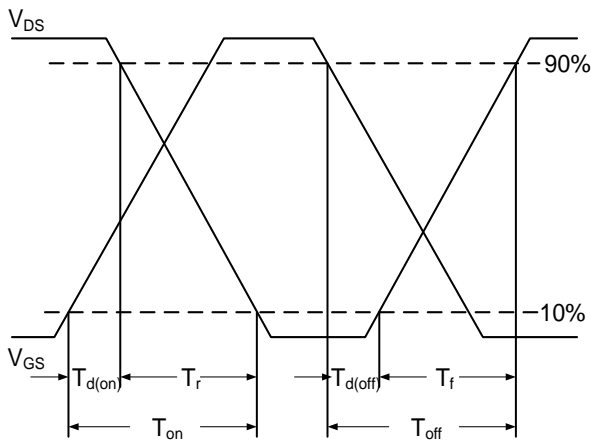
**Fig.6 Turn-On Resistance vs.  $I_D$**



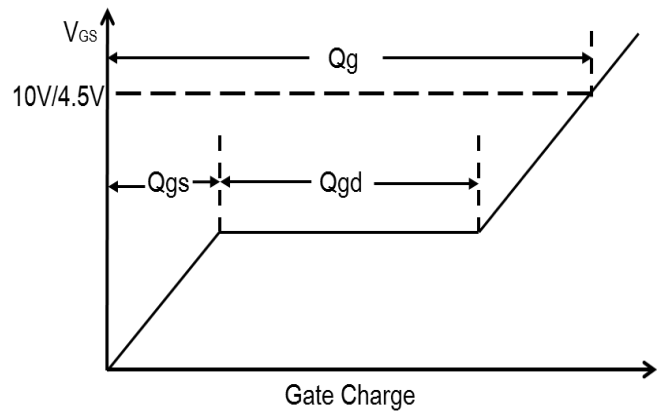
**Fig.7 Normalized Transient Impedance**



**Fig.8 Maximum Safe Operation Area**



**Fig.9 Switching Time Waveform**



**Fig.10 Gate Charge Waveform**

TO263 PACKAGE INFORMATION

